

FEATURE

Power dissipation

$$P_{CM} : 0.625 \text{ W } T_{amb}=25^{\circ}\text{C}$$

Collector current

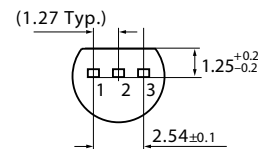
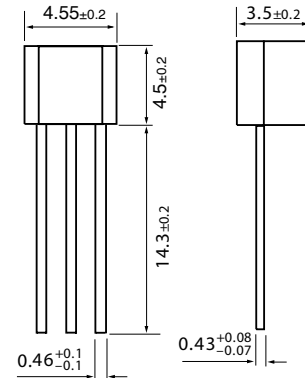
$$I_{CM} : 0.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 40 \text{ V}$$

Operating and storage junction temperature range

$$T_j, T_{stg} : -55 \text{ to } +150^{\circ}\text{C}$$

TO-92


- 1: Emitter
- 2: Base
- 3: Collector

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}, I_C = 50\text{mA}$	64		300	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50\text{mA}$			0.6	V
Base-emitter voltage	$V_{BE(sat)}$	$I_C = 500 \text{ mA}, I_B = 50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 6\text{V}, I_C = 20\text{mA}, f = 30\text{MHz}$	150			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	D	E	F	G	H	I
Range	64-91	78-112	96-135	112-166	144-202	190-300

Typical Characteristics

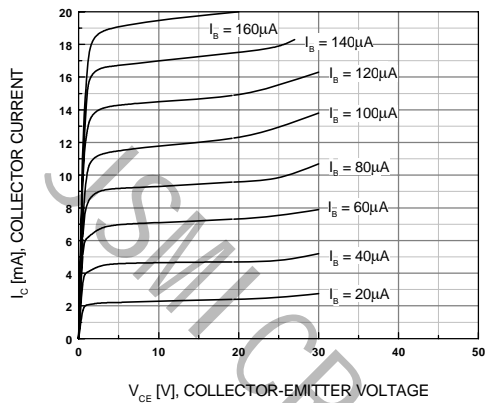


Figure 1. Static Characteristic

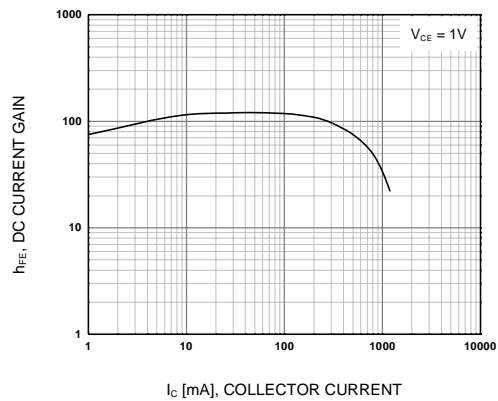


Figure 2. DC current Gain

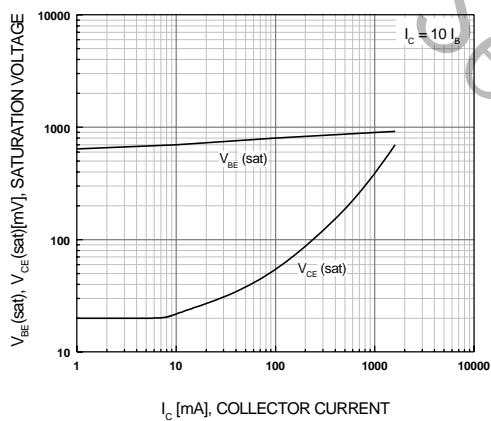


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

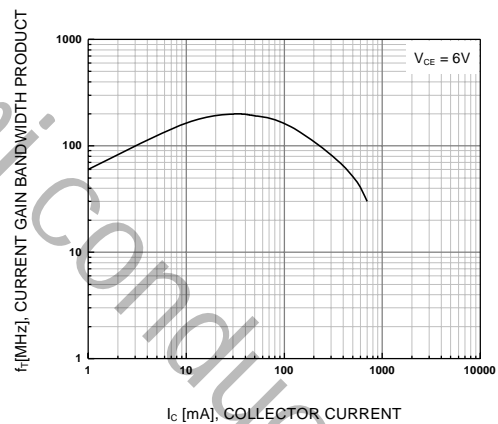


Figure 4. Current Gain Bandwidth Product

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)